

**Amendments to the Claims:**

This listing of claims will replace all prior versions and listings of claims in the application:

**Listing of Claims:**

Claims 1-6 are canceled.

7. (currently amended) A method for fabricating a laminated magnetic shield for an MR read head comprising:
- providing a substrate;
- forming on said substrate a layer of Al<sub>2</sub>O<sub>3</sub> of thickness between 0.5 microns and 10.0 microns;
- forming on said Al<sub>2</sub>O<sub>3</sub> layer a first layer of ferromagnetic material;
- forming on said first layer of ferromagnetic material a layer of ruthenium;
- forming on said layer of ruthenium a second layer of ferromagnetic material;
- forming on said second layer of ferromagnetic material a dielectric layer;
- wherein the layer of ruthenium [[if]] is of thickness between 2.0 angstroms and 4.0 angstroms.

Claims 8-19 are canceled.

20. (currently amended) A method for fabricating a laminated magnetic shield for an MR read head comprising:

providing a substrate;

forming on said substrate a first layer of ferromagnetic material;

forming on said first layer of ferromagnetic material a first layer of CoFe;

forming on said first layer of CoFe a layer of ruthenium (Ru);

forming on said layer of ruthenium a second layer of CoFe;

forming on said second layer of CoFe a second layer of ferromagnetic material;

forming on said second layer of ferromagnetic material a dielectric layer;

wherein the layer of ruthenium [[if]] is of thickness between 2.0 angstroms and 4.0 angstroms.

Claims 21-31 are canceled.

32. (currently amended) A laminated magnetic shield for an MR read head comprising:

a substrate;

a layer of Al<sub>2</sub>O<sub>3</sub> of thickness between 0.5 microns and 10.0 microns formed on said substrate;

a first layer of ferromagnetic material formed on said layer of Al<sub>2</sub>O<sub>3</sub>;

a layer of ruthenium formed on said first layer of ferromagnetic material;

a second layer of ferromagnetic material formed on said layer of ruthenium;  
a dielectric layer formed on said second layer of ferromagnetic material;  
wherein the layer of ruthenium [[if]] is of thickness between 2.0 angstroms and  
4.0 angstroms.

Claims 33-43 are canceled.

44. (currently amended) A laminated magnetic shield for an MR read head comprising:  
a substrate;  
a first layer of ferromagnetic material formed on said substrate;  
a first layer of CoFe formed on said first layer of ferromagnetic material;  
a layer of ruthenium formed on said first layer of CoFe;  
a second layer of CoFe formed on said layer of ruthenium;  
a second layer of ferromagnetic material formed on said second layer of CoFe;  
a dielectric layer formed on said second layer of ferromagnetic material;  
wherein the layer of ruthenium [[if]] is of thickness between 2.0 angstroms and  
4.0 angstroms.

Claims 45-51 are canceled.

58. (currently amended) A magnetoresistive read head with laminated magnetic shields comprising:

a first laminated magnetic shield;  
a magnetoresistive sensor element formed on said first laminated magnetic shield;  
a second laminated magnetic shield formed on said magnetoresistive sensor;  
wherein the first laminated magnetic shield comprises:  
a substrate;  
a layer of Al<sub>2</sub>O<sub>3</sub> of thickness between 0.5 microns and 10.0 microns  
formed on said substrate;  
a first layer of ferromagnetic material formed on said layer of Al<sub>2</sub>O<sub>3</sub>;  
a layer of ruthenium formed on said first layer of ferromagnetic material;  
a second layer of ferromagnetic material formed on said layer of  
ruthenium;  
a dielectric layer formed on said second layer of ferromagnetic material;  
wherein the layer of ruthenium [[if]] is of thickness between 2.0 angstroms  
and 4.0 angstroms.

Claims 59-69 are canceled.

70. (currently amended) A magnetoresistive read head with laminated magnetic shields comprising:  
a first laminated magnetic shield;  
a magnetoresistive sensor element formed on said first laminated magnetic shield;  
a second laminated magnetic shield formed on said magnetoresistive sensor  
element;

wherein the first laminated magnetic shield comprises:

- a substrate;
  - a first layer of ferromagnetic material formed on said substrate;
  - a first layer of CoFe formed on said first layer of ferromagnetic material;
  - a layer of ruthenium formed on said first layer of CoFe;
  - a second layer of CoFe formed on said layer of ruthenium;
  - a second layer of ferromagnetic material formed on said second layer of CoFe;
  - a dielectric layer formed on said second layer of ferromagnetic material;
- wherein the layer of ruthenium [[if]] is of thickness between 2.0 angstroms and 4.0 angstroms.

Claims 71-82 are canceled..

83. (currently amended) A magnetoresistive read head with laminated magnetic shields comprising:

- a first laminated magnetic shield;
  - a magnetoresistive sensor element formed on said first laminated magnetic shield;
  - a second laminated magnetic shield formed on said magnetoresistive sensor element;
- wherein the second laminated magnetic shield comprises:
- a substrate;

a layer of Al<sub>2</sub>O<sub>3</sub> of thickness between 0.5 microns and 10 microns formed on said substrate;

a first layer of ferromagnetic material formed on said layer of Al<sub>2</sub>O<sub>3</sub>;

a layer of ruthenium formed on said first layer of ferromagnetic material;

a second layer of ferromagnetic material formed on said layer of ruthenium;

a dielectric layer formed on said second layer of ferromagnetic material;

wherein the layer of ruthenium [[if]] is of thickness between 2.0 angstroms and 4.0 angstroms.

Claims 84-94 are canceled.

95. (currently amended) A magnetoresistive read head with laminated magnetic shields comprising:

a first laminated magnetic shield;

a magnetoresistive sensor element formed on said first laminated magnetic shield;

a second laminated magnetic shield formed on said magnetoresistive sensor element;

wherein the second laminated magnetic shield comprises:

a substrate;

a first layer of ferromagnetic material formed on said substrate;

a first layer of CoFe formed on said first layer of ferromagnetic material;

a layer of ruthenium formed on said first layer of CoFe;

a second layer of CoFe formed on said layer of ruthenium;

a second layer of ferromagnetic material formed on said second layer of

CoFe;

a dielectric layer formed on said second layer of ferromagnetic material;

wherein the layer of ruthenium [[if]] is of thickness between 2.0 angstroms

and 4.0 angstroms.